

Notice of References Cited	Application/Control No. 10/092,887	Applicant(s)/Patent Under Reexamination BRANDES ET AL.	
	Examiner Scott R. Wilson	Art Unit 2826	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,831,324	11-1998	Bang, Il-soon	257/508
	C	US-5,425,860	06-1995	Truher et al.	204/192.23
	D	US-4,109,271	08-1978	Pankove, Jacques Isaac	257/53
	E	US-5,426,412	06-1995	Tomonari et al.	338/18
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	M	US-			

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NON-PATENT DOCUMENTS

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	U	Gail Dewey, "Morton Announces Low Resistivity Components for Semiconductor Manufacturing", 18 June 1999, Rohm and Haas Co. Press Release and CVD Silicon Carbide Data Sheet.
	V	Nagai et al., "SiC Thin Film Thermistor", Thin Solid Films, Vol. 125, (October 11, 1984), pp. 355-359.
	W	Wahab et al., "Growth of epitaxial 3C-SiC films on (111) silicon substrates at 850 deg C by reactive magnetron sputtering", Journal of Applied Physics, Vol. 74, Issue 3, (August 1, 1993), pp. 1663-1669.
	X	Kortright et al., "Amorphous silicon carbide coatings for extreme ultraviolet optics", 15 July 1988, Applied Optics, Vol. 27, No. 14, pp. 2841-2846.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.